

NextPower 100 V, 9 m Ω N-channel MOSFET in LFPAK56 package

1 November 2017

Product data sheet

1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

2. Features and benefits

- Low Q_{rr} for higher efficiency and lower spiking
- Qualified to 175 °C
- Low Q_G x R_{DSon} FOM for high efficiency switching applications
- Strong avalanche energy rating (E_{as})
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPAK56 package
- Wave-solderable LFPAK56 package

3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- BLDC motor control
- USB-PD and mobile fast-charge adapters
- LED lighting
- Full-bridge and half-bridge applications
- Flyback and resonant topologies

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	90	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	198	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics	·	· ·			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	7.2	9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 11	-	10.7	14	mΩ
Dynamic ch	naracteristics	·				
Q _{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V;	-	7.5	-	nC
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13	-	38.5	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
Avalanche ruggedness								
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} {\sf I}_{D} = 30.3 \; {\sf A}; \; {\sf V}_{sup} \leq \; 100 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {\rm ^{\circ}C}; \; \underline{{\sf Fig. 4}}; \\ {\sf Unclamped} \end{array} $	[1]	-	-	234	mJ	
Source-drain diode								
Q _r	recovered charge	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 50 \text{ V}; \frac{\text{Fig. 16}}{16}$		-	52.6	-	nC	

[1] Protected by 100% test

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	ل ا دے ب ا	
3	S	source	a	G
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	ī 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN8R7-100YSF	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN8R7-100YSF	8F7S10

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8. Limiting values

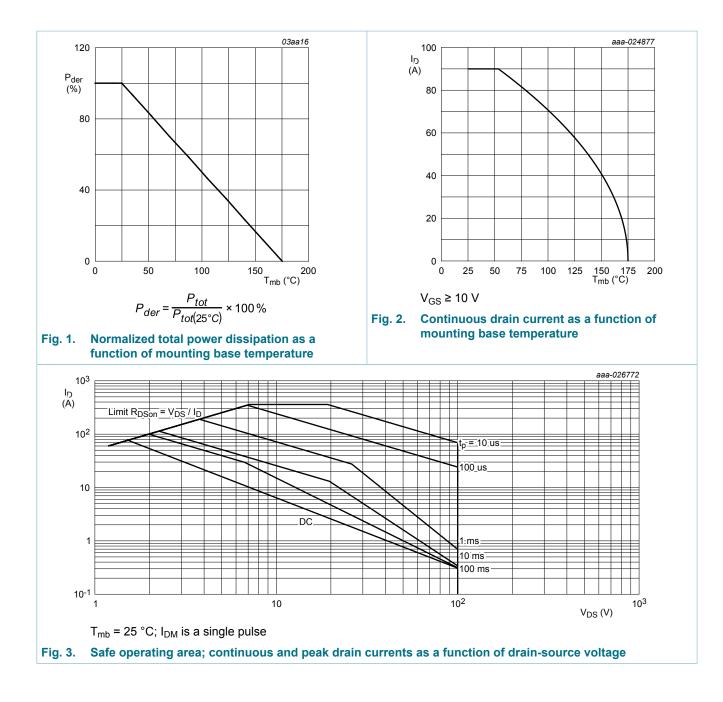
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	198	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	90	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	71	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	360	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C		-	90	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	360	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_{D} = 30.3 \; \text{A}; \; V_{sup} \leq \; 100 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \overline{\text{Fig. 4}}; \\ \text{Unclamped} \end{array} $	[1]	-	234	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega$	[1]	-	30.3	А

[1] Protected by 100% test

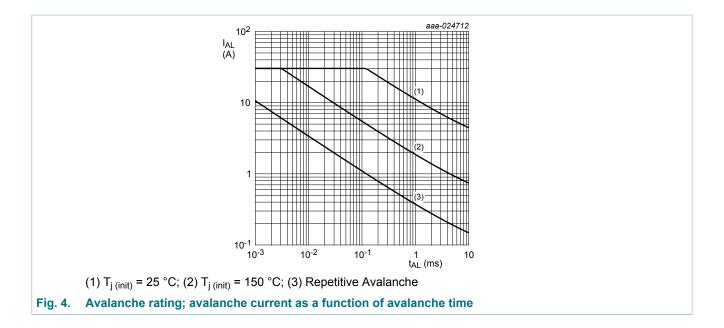
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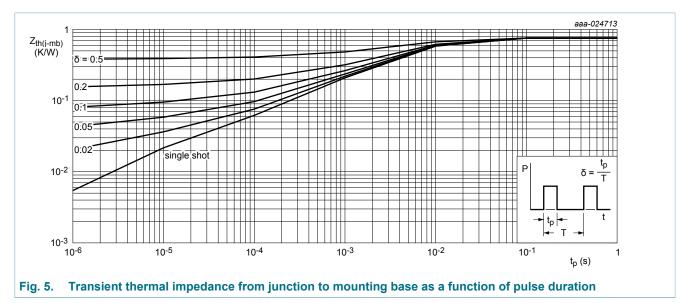
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.67	0.76	K/W



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10. Characteristics

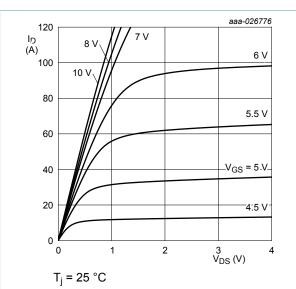
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C	-	3.6	-	V
	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C	-	1.9	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9</u>	2	3.1	4	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 175 °C	-	-8	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	5	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	5	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	5	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	-	7.2	9	mΩ
		V_{GS} = 7 V; I _D = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	8.2	13.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; <u>Fig. 11</u>	-	10.7	14	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; <u>Fig. 11</u>	-	15.8	19.8	mΩ
R _G	gate resistance	f = 1 MHz	-	0.8	-	Ω
Dynamic cha	racteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 12; Fig. 13	-	38.5	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	19.8	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	12.8	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	7.7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	5.1	-	nC
Q _{GD}	gate-drain charge		-	7.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 50 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.9	-	V
C _{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz;	-	2758	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	532	-	pF
C _{rss}	reverse transfer capacitance		-	17	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	12.5	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	11	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _{d(off)}	turn-off delay time			-	22.5	-	ns
t _f	fall time			-	12.7	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 50 V; <u>Fig. 16</u>		-	45.5	-	ns
Qr	recovered charge			-	52.6	-	nC



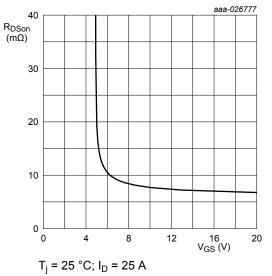
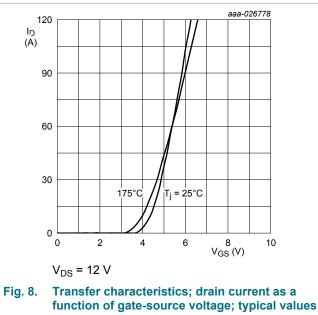
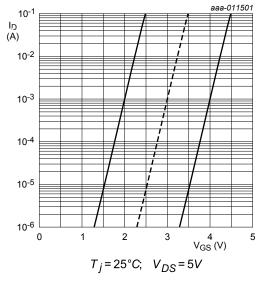


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



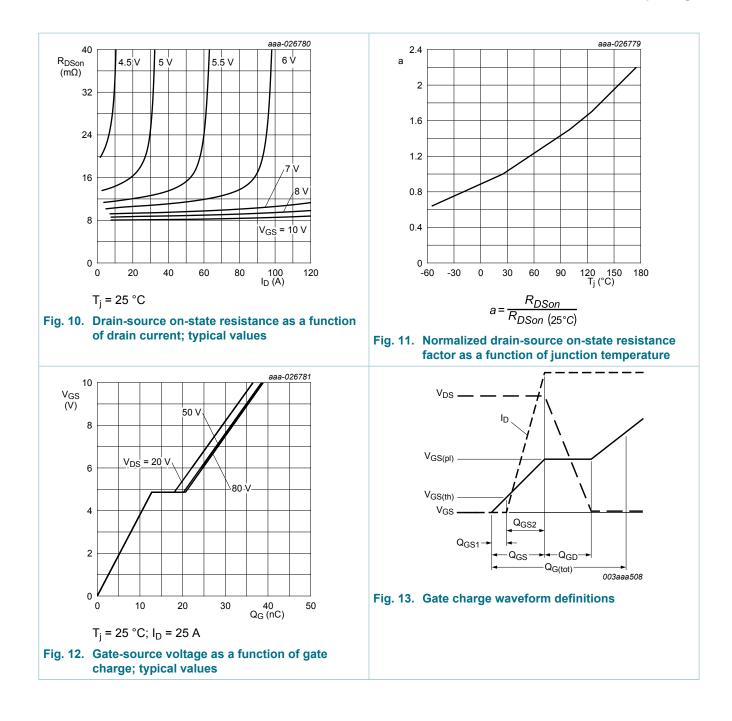




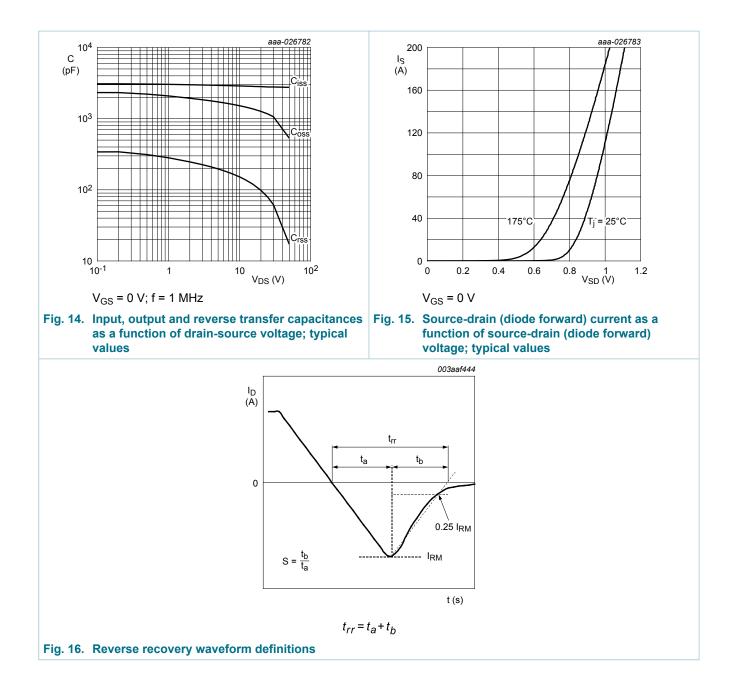


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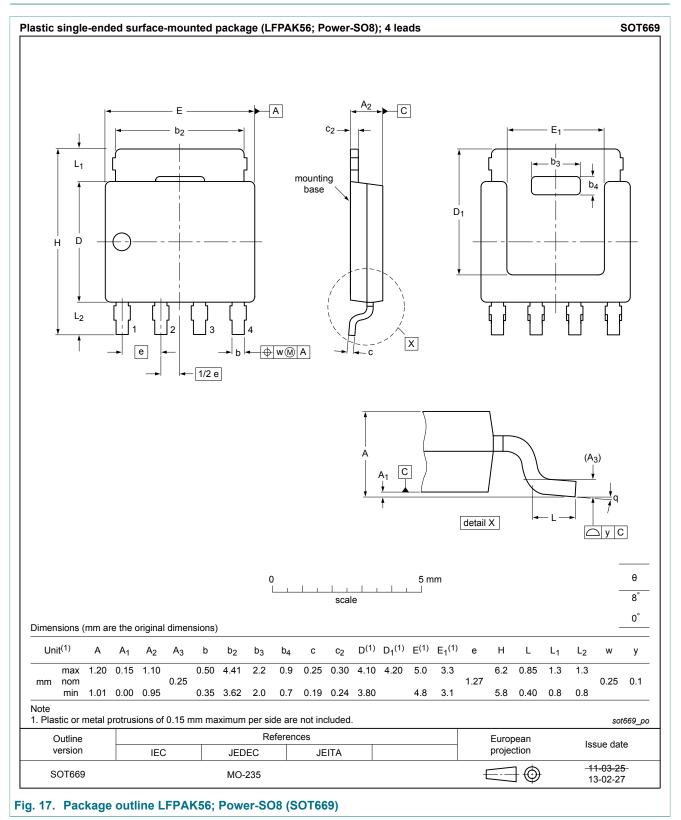


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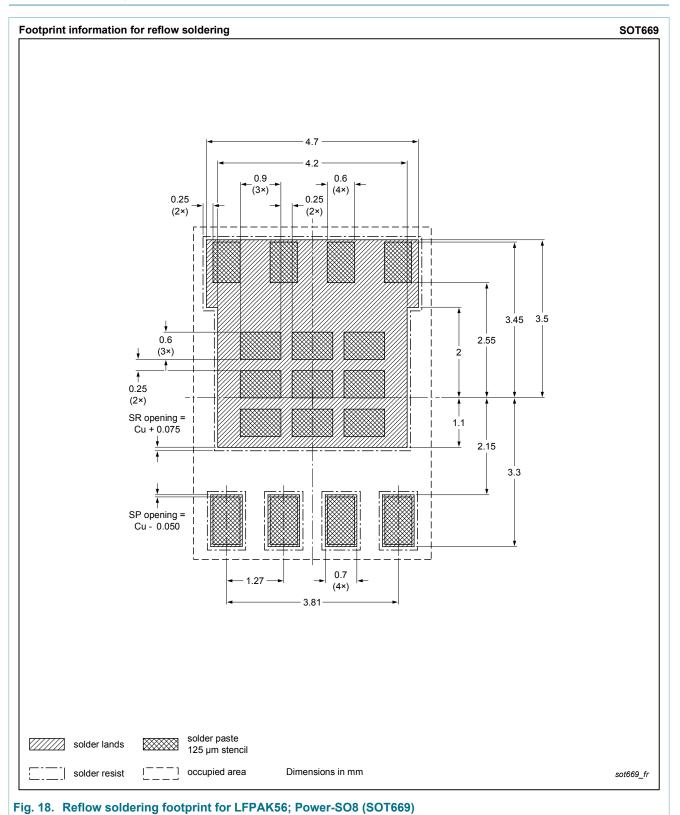
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11. Package outline



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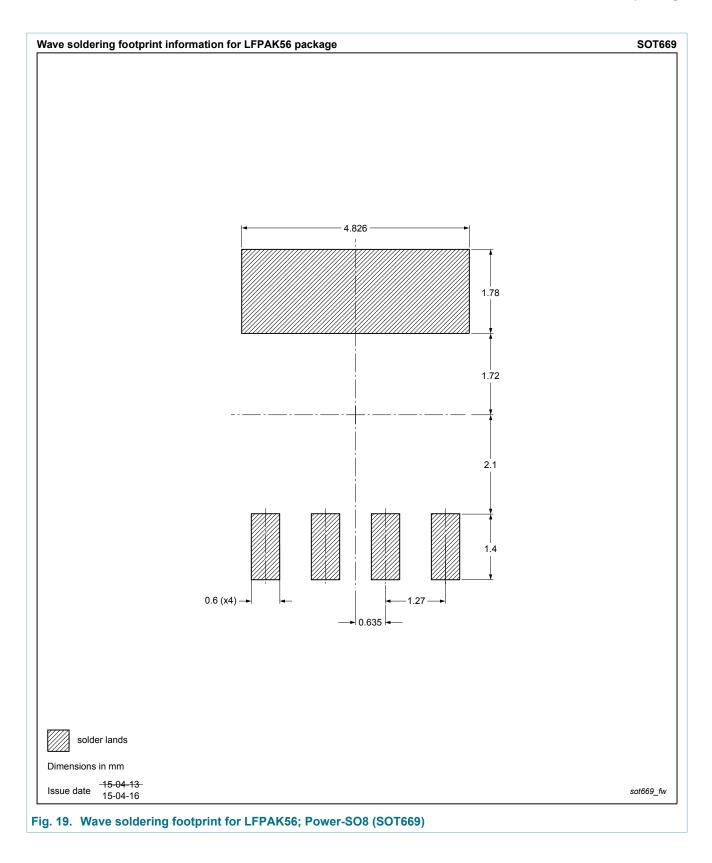
12. Soldering



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13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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